

Precision Monolithics Inc.

FEATURES (All Devices)

- Significant Performance Advantages over LF155, 156 and 157 Devices.
- Low Input Offset Voltage $500\mu V$ Max
- Low Input Offset Voltage Drift $2.0\mu V/\text{°C}$
- Minimum Slew Rate Guaranteed on All Models
- Temperature-Compensated Input Bias Currents
- Guaranteed Input Bias Current @ 125°C
- Bias Current Specified WARMED UP Over Temperature
- Internal Compensation
- Low Input Noise Current $0.01\text{pA}/\sqrt{\text{Hz}}$
- High Common-Mode Rejection Ratio 100dB
- Models With MIL-STD-883 Processing Available
- 125°C Temperature Tested DICE

OP-15

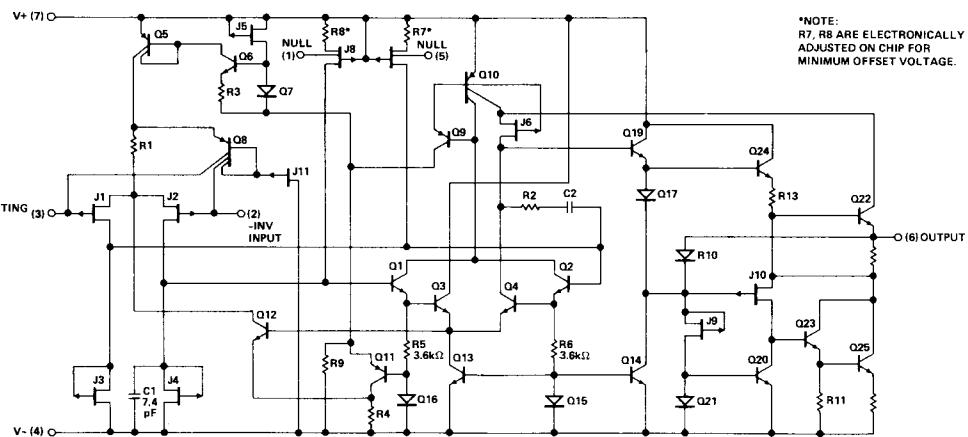
- 156 Speed With 155 Dissipation (80mW Typ)
- Wide Bandwidth 6MHz
- High Slew Rate $13V/\mu s$
- Fast Settling to $\pm 0.1\%$ 1200ns
- Available in Die Form

OP-16

- Higher Slew Rate $25V/\mu s$
- Faster Settling to $\pm 0.1\%$ 900ns
- Wider Bandwidth 8MHz
- Available in Die Form

OP-17

- Highest Slew Rate $60V/\mu s$
- Fastest Settling to $\pm 0.1\%$ 600ns
- Highest Gain Bandwidth Product ($A_{VCL} = 5$ Min) 30MHz
- Available in Die Form

SIMPLIFIED SCHEMATIC

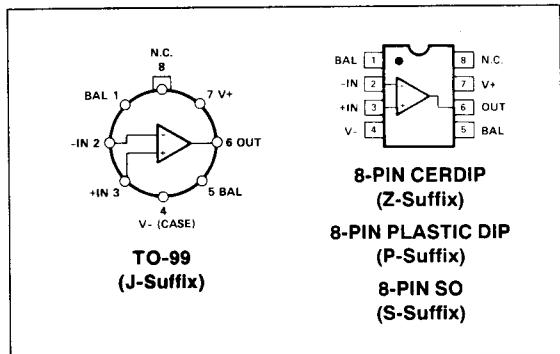
ORDERING INFORMATION[†]

$T_A = +25^\circ\text{C}$		PACKAGE			OPERATING TEMPERATURE RANGE
V_{os} MAX (mV)	TO-99	CERDIP 8-PIN	PLASTIC 8-PIN	SO 8-PIN	
0.5	OP15AJ*	OP15AZ*	-	-	MIL
	OP16AJ*	-	-	-	
	OP17AJ*	OP17AZ*	-	-	
0.5	OP15EJ	OP15EZ	-	-	COM
	OP16EJ	OP16EZ	-	-	
	OP17EJ	OP17EZ	-	-	
1.0	OP15BJ/883	OP15BZ/883	-	-	MIL
	OP16BJ/883	OP16BZ/883	-	-	
	OP17BJ*	OP17BZ	-	-	
1.0	OP15FJ	OP15FZ	OP15FP	-	COM
	OP16FJ	OP16FZ	OP16FP	-	
	-	-	OP17FP	-	
3.0	-	OP17CJ/883	-	-	MIL
	OP15GJ	OP15GZ	OP15GP	OP15GS	
	OP16GJ	OP16GZ	OP16GP	OP16GS	XIND
3.0	OP17GJ	OP17GZ	OP17GP	OP17GS	

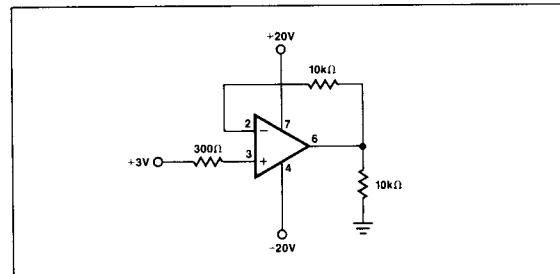
* For devices processed in total compliance to MIL-STD-883, add /883 after part number. Consult factory for 883 data sheet.

† Burn-in is available on commercial and industrial temperature range parts in CerDIP, plastic DIP, and TO-can packages. For ordering information, see 1990/91 Data Book, Section 2.

PIN CONNECTIONS



BURN-IN CIRCUIT



ABSOLUTE MAXIMUM RATINGS (Note 1)

Supply Voltage

All Devices Except C, G (Packaged) & GR Grades	$\pm 22\text{V}$
C, G (Packaged) & GR Grades	$\pm 18\text{V}$

Operating Temperature

A, B, & C Grades	-55°C to $+125^\circ\text{C}$
E & F Grades	0°C to $+70^\circ\text{C}$
G Grade	-40°C to $+85^\circ\text{C}$

Maximum Junction Temperature

$+150^\circ\text{C}$

DICE Junction Temperature (T_j)

-65°C to $+150^\circ\text{C}$

Differential Input Voltage

All Devices Except C, G (Packaged) & GR Grades	$\pm 40\text{V}$
C, G (Packaged) & GR Grades	$\pm 30\text{V}$

Input Voltage (Note 2)

All Devices Except C, G (Packaged) & GR Grades	$\pm 20\text{V}$
C, G (Packaged) & GR Grades	$\pm 16\text{V}$

Input Voltage

OP-15A, OP-15B, OP-15E, OP-15F	$\pm 20\text{V}$
OP-15G	$\pm 16\text{V}$
OP-16A, OP-16B, OP-16E, OP-16F	$\pm 20\text{V}$
OP-16C, OP-16G	$\pm 16\text{V}$
OP-17A, OP-17B, OP-17E, OP-17F	$\pm 20\text{V}$
OP-17C, OP-17G	$\pm 16\text{V}$

Output Short-Circuit Duration

Indefinite

Storage Temperature Range

-65°C to $+150^\circ\text{C}$

Lead Temperature Range (Soldering, 60 sec)

$+300^\circ\text{C}$

PACKAGE TYPE	Θ_{JA} (Note 3)	Θ_{JC}	UNITS
TO-99 (J)	150	18	°C/W
8-Pin Hermetic DIP (Z)	148	16	°C/W
8-Pin Plastic DIP (P)	103	43	°C/W
8-Pin SO (S)	158	43	°C/W

NOTES:

1. Absolute maximum ratings apply to both DICE and packaged parts, unless otherwise noted.
2. Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power-supply voltage.
3. Θ_{JA} is specified for worst case mounting conditions, i.e., Θ_{JA} is specified for device in socket for TO, CerDIP and P-DIP packages; Θ_{JA} is specified for device soldered to printed circuit board for SO package.

ELECTRICAL CHARACTERISTICS at $V_S = \pm 15V$, $T_A = 25^\circ C$, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	OP-15A/E			OP-15B/F			OP-15G			
			OP-16A/E			OP-16B/F			OP-16C/G			
			OP-17A/E			OP-17B/F			OP-17C/G			
Input Offset Voltage	V_{OS}	$R_S = 50\Omega$	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Current	I_{OS}	$T_j = 25^\circ C$: Note 1, Device Operating	—	0.2	0.5	—	0.4	1.0	—	0.5	3.0	
		$T_j = 25^\circ C$: Note 1, Device Operating	OP-15	—	3	10	—	6	20	—	12	50
Input Bias Current	I_B	$T_j = 25^\circ C$: Note 1, Device Operating	OP-15	—	5	22	—	10	40	—	20	100
		$T_j = 25^\circ C$: Note 1, Device Operating	OP-16/OP-17	—	3	10	—	6	20	—	12	50
Input Resistance	R_{IN}	$T_j = 25^\circ C$: Note 1, Device Operating	OP-15	—	15	50	—	30	100	—	60	200
		$T_j = 25^\circ C$: Note 1, Device Operating	OP-16/OP-17	—	18	110	—	40	200	—	80	400
Input Resistance	R_{IN}	$T_j = 25^\circ C$: Note 1, Device Operating	OP-15	—	15	50	—	30	100	—	60	200
		$T_j = 25^\circ C$: Note 1, Device Operating	OP-16/OP-17	—	20	130	—	40	250	—	80	500
Large-Signal Voltage Gain	A_{VO}	$R_L \geq 2k\Omega$ $V_O = \pm 10V$	100	240	—	75	220	—	50	200	—	V/mV
Output Voltage Swing	V_O	$R_L = 10k\Omega$	±12	±13	—	±12	±13	—	±12	±13	—	V
		$R_L = 2k\Omega$	±11	±12.7	—	±11	±12.7	—	±11	±12.7	—	V
Supply Current	I_{SY}	OP-15	—	2.7	4.0	—	2.7	4.0	—	2.8	5.0	mA
		OP-16/OP-17	—	4.6	7.0	—	4.6	7.0	—	4.8	8.0	mA
Slew Rate	SR	$A_{VCL} = +1$: Note 3	OP-15	10	13	—	7.5	11	—	5	9	—
		OP-16	18	25	—	12	21	—	9	17	—	V/ μ s
		$A_{VCL} = +5$: Note 3	OP-17	45	60	—	35	50	—	25	40	—
Gain Bandwidth Product	GBW	OP-15	4.0	6.0	—	3.5	5.7	—	3.0	5.4	—	MHz
		OP-16	6.0	8.0	—	5.5	7.6	—	5.0	7.2	—	MHz
Closed-Loop Bandwidth	CLBW	OP-17	20	30	—	15	28	—	11	26	—	MHz
		OP-15	—	14	—	—	13	—	—	12	—	—
Settling Time	t _S	OP-16	—	19	—	—	18	—	—	17	—	MHz
		OP-17	—	11	—	—	10	—	—	9	—	—
		OP-15	—	4.5	—	—	4.5	—	—	4.7	—	—
Settling Time	t _S	OP-15	—	1.5	—	—	1.5	—	—	1.6	—	—
		OP-16	—	1.2	—	—	1.2	—	—	1.3	—	—
		OP-17	—	0.9	—	—	0.9	—	—	1.0	—	—
Settling Time	t _S	OP-15	—	3.8	—	—	3.8	—	—	4.0	—	—
		OP-16	—	1.2	—	—	1.2	—	—	1.3	—	—
		OP-17	—	0.9	—	—	0.9	—	—	1.0	—	—
Settling Time	t _S	OP-15	—	1.5	—	—	1.5	—	—	1.6	—	—
		OP-16	—	0.7	—	—	0.7	—	—	0.8	—	—
		OP-17	—	0.6	—	—	0.6	—	—	0.7	—	—
Input Voltage Range	IVR	—	±10.5	—	—	—	±10.5	—	—	±10.3	—	—
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 10.5V$	86	100	—	86	100	—	—	—	—	dB
		$V_{CM} = \pm 10.3V$	—	—	—	—	—	—	82	96	—	—
Power Supply Rejection Ratio	PSRR	$V_S = \pm 10V$ to $\pm 18V$	—	10	51	—	10	51	—	—	—	μ V/V
		$V_S = \pm 10V$ to $\pm 15V$	—	—	—	—	—	—	—	10	80	—
Input Noise Voltage Density	e _n	$f_O = 100Hz$	—	20	—	—	20	—	—	20	—	nV/ \sqrt{Hz}
		$f_O = 1000Hz$	—	15	—	—	15	—	—	15	—	—
Input Noise Current Density	i _n	$f_O = 100Hz$	—	0.01	—	—	0.01	—	—	0.01	—	pA/ \sqrt{Hz}
		$f_O = 1000Hz$	—	0.01	—	—	0.01	—	—	0.01	—	—
Input Capacitance	C _{IN}	—	3	—	—	—	3	—	—	3	—	pF

NOTES:

1. Input bias current is specified for two different conditions. The $T_j = 25^\circ C$ specification is with the junction at ambient temperature; the Device Operating specification is with the device operating in a warmed-up condition at $25^\circ C$ ambient. The warmed-up bias current value is correlated to the junction temperature value via the curves of I_B vs T_j and I_B vs T_A . PMI has a bias current compensation circuit which gives improved bias current over the standard JFET input op amps. I_B and I_{OS} are measured at $V_{CM} = 0$.
2. Settling time is defined here for a unity gain inverter connection using $2k\Omega$ resistors. It is the time required for the error voltage at the voltage at the

inverting input pin on the amplifier to settle to within a specified percent of its final value from the time a 10V step input is applied to the inverter. See settling time test circuit.

3. Sample tested.
4. Settling time is defined here for an $A_V = -5$ connection with $R_F = 2k\Omega$. It is the time required for the error voltage at the inverting input pin on the amplifier to settle to within 0.01% of its final value from the time a 2V step input is applied to the inverter. See settling time test circuit.

ELECTRICAL CHARACTERISTICS at $V_S = \pm 15V$, $-55^\circ C \leq T_A \leq 125^\circ C$, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	OP-15A			OP-15B			OP-16C			
			OP-16A			OP-16B			OP-17C			
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	V_{OS}	$R_S = 50\Omega$	—	0.4	0.9	—	0.7	2.0	—	0.9	4.5	
Average Input Offset Voltage Drift		Note 2										
Without External Trim	TCV_{OS}		—	2	5	—	3	10	—	4	15	
With External Trim	TCV_{OSn}	$R_P = 100k\Omega$	—	2	—	—	3	—	—	4	—	
Input Offset Current Current Note 1	I_{OS}	$T_j = 125^\circ C$	—	0.6	4.0	—	0.8	6.0	—	1.0	9.0	
		$T_A = 125^\circ C$	OP-15	—	0.8	7.0	—	1.2	11	—	1.5	17
		$T_j = 125^\circ C$	OP-16/OP-17	—	0.6	4.0	—	0.8	6.0	—	1.0	9.0
		$T_A = 125^\circ C$	Device Operating	—	1.0	8.5	—	1.3	14.5	—	1.7	22
Input Bias Current Current Note 1	I_B	$T_j = 125^\circ C$	OP-15	—	± 1.2	± 5.0	—	± 1.5	± 7.5	—	± 1.8	± 10
		$T_A = 125^\circ C$	Device Operating	—	± 1.7	± 9.0	—	± 2.2	± 14	—	± 2.7	± 19
		$T_j = 125^\circ C$	OP-16/OP-17	—	± 1.2	± 5.0	—	± 1.5	± 7.5	—	± 1.8	± 10
		$T_A = 125^\circ C$	Device Operating	—	± 2.0	± 11	—	± 2.5	± 18	—	± 3.0	± 25
Input Voltage Range	IVR		± 10.4	—	—	± 10.4	—	—	± 10.25	—	—	
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 10.4V$	85	97	—	85	97	—	—	—	—	
		$V_{CM} = \pm 10.25V$	—	—	—	—	—	—	80	93	—	
Power Supply Rejection Ratio	PSRR	$V_S = \pm 10V$ to $\pm 18V$	—	15	57	—	15	57	—	—	—	
		$V_S = \pm 10V$ to $\pm 15V$	—	—	—	—	—	—	—	23	100	
Large-Signal Voltage Gain	A_{VO}	$R_L \geq 2k\Omega$ $V_O = \pm 10V$	35	120	—	30	110	—	25	100	—	
Output Voltage Swing	V_O	$R_L \geq 10k\Omega$	± 12	± 13	—	± 12	± 13	—	± 12	± 13	—	
											V	

NOTES:

1. Input bias current is specified for two different conditions. The $T_j = 25^\circ C$ specification is with the junction at ambient temperature; the Device Operating specification is with the device operating in a warmed-up condition at $25^\circ C$ ambient. The warmed-up bias current value is correlated to the junction temperature value via the curves of I_B vs T_j and I_B vs T_A . PMI has a bias current compensation circuit which gives improved bias current over the standard JFET input op amps. I_B and I_{OS} are measured at $V_{CM} = 0$.
2. Sample tested.

ELECTRICAL CHARACTERISTICS at $V_S = \pm 15V$, $0^\circ C \leq T_A \leq 70^\circ C$ for E and F, $-40 \leq T_A \leq +85^\circ C$ for G grade, unless otherwise noted.

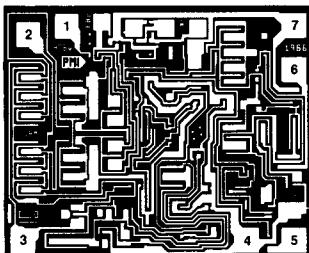
PARAMETER	SYMBOL	CONDITIONS	OP-15E OP-16E OP-17E			OP-15F OP-16F OP-17F			OP-15G OP-16G OP-17G			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	V_{OS}	$R_S = 50\Omega$	—	0.3	0.75	—	0.55	1.5	—	0.7	3.8	mV
Average Input Offset Voltage Drift												
Without External Trim	TCV_{OS}		—	2	5	—	3	10	—	4	30	(Note 2)
With External Trim	TCV_{OSn}	$R_P = 100k\Omega$	—	2	—	—	3	—	—	4	—	$\mu V/\text{ }^\circ C$
Input Offset Current (Note 1)	I_{OS}	$T_j = 70^\circ C$ $T_A = 70^\circ C$ Device Operating	OP-15	—	0.04	0.30	—	0.06	0.45	—	0.08	0.65
		$T_j = 70^\circ C$ $T_A = 70^\circ C$ Device Operating	OP-16/OP-17	—	0.06	0.55	—	0.08	0.80	—	0.10	1.2
		$T_j = 70^\circ C$ $T_A = 70^\circ C$ Device Operating	OP-15	—	0.04	0.30	—	0.06	0.45	—	0.08	0.65
		$T_j = 70^\circ C$ $T_A = 70^\circ C$ Device Operating	OP-16/OP-17	—	0.07	0.70	—	0.10	1.1	—	0.15	1.7
Input Bias Current (Note 1)	I_B	$T_j = 70^\circ C$ $T_A = 70^\circ C$ Device Operating	OP-15	—	± 0.10	± 0.40	—	± 0.12	± 0.60	—	± 0.14	± 0.80
		$T_j = 70^\circ C$ $T_A = 70^\circ C$ Device Operating	OP-16/OP-17	—	± 0.13	± 0.75	—	± 0.16	± 1.1	—	± 0.19	± 1.5
		$T_j = 70^\circ C$ $T_A = 70^\circ C$ Device Operating	OP-15	—	± 0.10	± 0.40	—	± 0.12	± 0.60	—	± 0.14	± 0.80
		$T_j = 70^\circ C$ $T_A = 70^\circ C$ Device Operating	OP-16/OP-17	—	± 0.15	± 0.90	—	± 0.20	± 1.4	—	± 0.25	± 2.0
Input Voltage Range	IVR		—	± 10.4	—	—	—	± 10.4	—	—	—	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 10.4V$	85	98	—	85	98	—	—	—	—	—
		$V_{CM} = \pm 10.25V$	—	—	—	—	—	—	80	94	—	dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 10V$ to $\pm 18V$	—	13	57	—	13	57	—	—	—	—
		$V_S = \pm 10V$ to $\pm 15V$	—	—	—	—	—	—	—	20	100	$\mu V/V$
Large-Signal Voltage Gain	A_{VO}	$R_L \geq 2k\Omega$ $V_O = \pm 10V$	65	200	—	50	180	—	35	160	—	V/mV
Output Voltage Swing	V_O	$R_L \geq 10k\Omega$	—	± 12	± 13	—	± 12	± 13	—	± 12	± 13	V

NOTES:

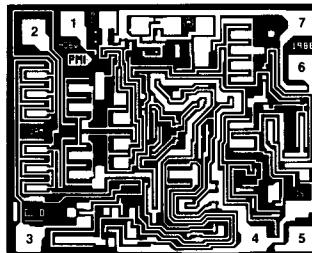
1. Input bias current is specified for two different conditions. The $T_j = 25^\circ C$ specification is with the junction at ambient temperature; the Device Operating specification is with the device operating in a warmed-up condition at $25^\circ C$ ambient. The warmed-up bias current value is correlated to the junction temperature value via the curves of I_B vs T_j and I_B vs T_A . PMI has a bias current compensation circuit which gives improved bias current over the standard JFET input op amps. I_B and I_{OS} are measured at $V_{CM} = 0$.
2. Sample tested.

DICE CHARACTERISTICS (125°C TESTED DICE AVAILABLE)

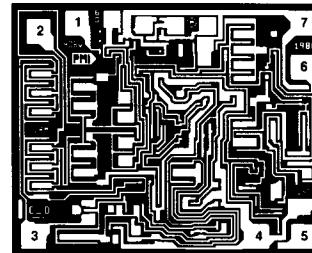
OP-15

DIE SIZE 0.068 × 0.056 inch, 3808 sq. mils
(1.73 × 1.42mm, 2.46 sq. mm)

OP-16

DIE SIZE 0.068 × 0.056 inch, 3808 sq. mils
(1.73 × 1.42mm, 2.46 sq. mm)

OP-17

DIE SIZE 0.068 × 0.056 inch, 3808 sq. mils
(1.73 × 1.42mm, 2.46 sq. mm)

1. BALANCE
2. INVERTING INPUT
3. NONINVERTING INPUT
4. V-
5. BALANCE
6. OUTPUT
7. V+

1. BALANCE
2. INVERTING INPUT
3. NONINVERTING INPUT
4. V-
5. BALANCE
6. OUTPUT
7. V+

1. BALANCE
2. INVERTING INPUT
3. NONINVERTING INPUT
4. V-
5. BALANCE
6. OUTPUT
7. V+

For additional DICE ordering information, refer to 1990/91 Data Book, Section 2.

WAFER TEST LIMITS at $V_S = \pm 15V$, $T_A = 25^\circ C$ for OP-15/16/17N, OP-15/16/17G and OP-15/16/17GR devices; $T_A = 125^\circ C$ for OP-15/16/17NT and OP-15/16/17GT devices, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	OP-15NT	OP-15N	OP-15GT	OP-15G	OP-15GR	UNITS
			OP-16NT	OP-16N	OP-16GT	OP-16G	OP-16GR	
Input Offset Voltage	V_{OS}	$R_S = 50\Omega$	0.9	0.5	2.0	1.0	3.0	mV MAX
Large-Signal Voltage Gain	A_{VO}	$V_O = \pm 10V$ $R_L = 2k\Omega$	35	100	30	75	50	V/mV MIN
Input Voltage Range	IVR		± 10.4	± 10.5	± 10.4	± 10.5	± 10.3	V MIN
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm IVR$	85	86	85	86	82	dB MIN
Power Supply Rejection Ratio	PSRR	$V_S = \pm 10V$ to $\pm 20V$ $V_S = \pm 10V$ to $\pm 15V$	57	51	57	51	—	$\mu V/V$ MAX
Output Voltage Swing	V_O	$R_L = 10k\Omega$ $R_L = 2k\Omega$	± 12	± 12	± 12	± 12	± 12	V MIN
Supply Current	I_{SY}	OP-15 OP-16, OP-17	—	4	—	4	5	mA MAX
Input Bias Current	I_B	OP-15 OP-16, OP-17	± 9 ± 11	—	± 14 ± 18	—	—	nA MAX
Input Offset Current	I_{OS}	OP-15 OP-16, OP-17	7.0 8.5	—	11.0 14.5	—	—	nA MAX

NOTES:

For 25°C characteristics of OP-15/16/17NT and OP-15/16/17GT, see OP-15/16/17N and OP-15/16/17G characteristics, respectively.

Electrical tests are performed at wafer probe to the limits shown. Due to variations in assembly methods and normal yield loss, yield after packaging is not guaranteed for standard product dice. Consult factory to negotiate specifications based on dice lot qualification through sample lot assembly and testing.

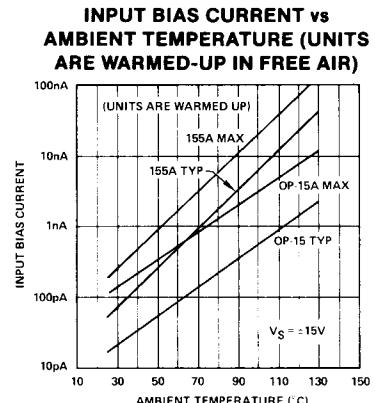
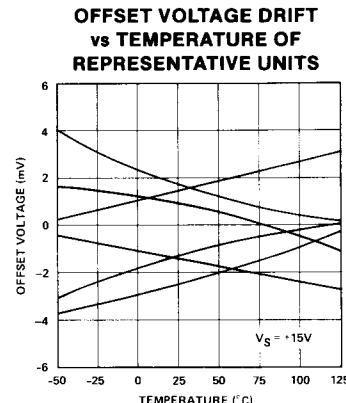
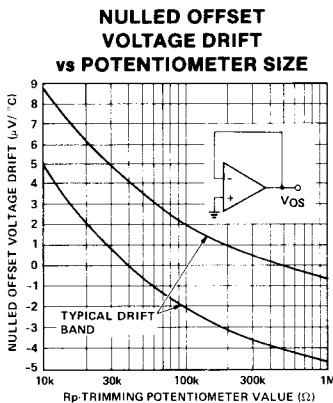
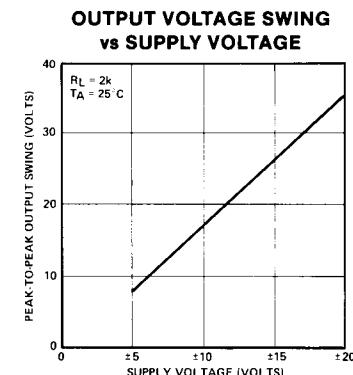
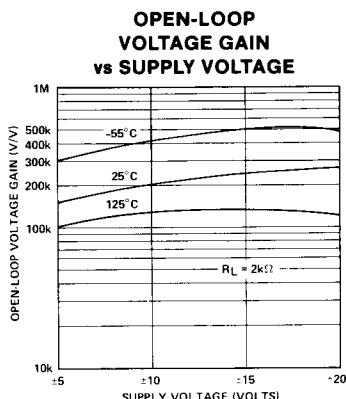
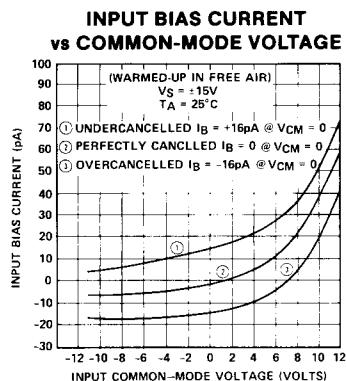
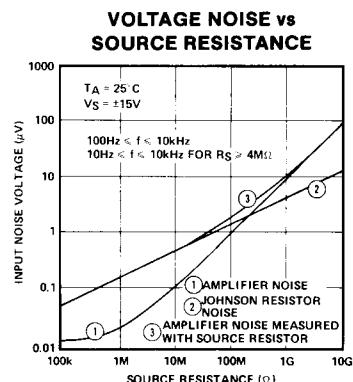
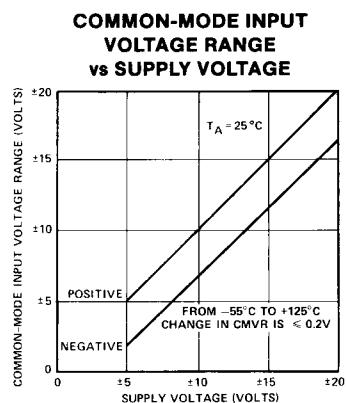
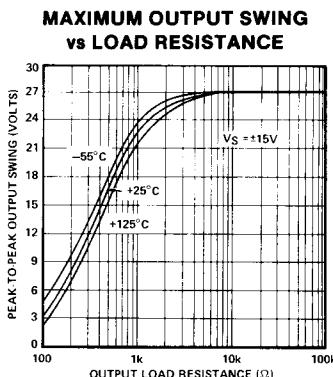
TYPICAL ELECTRICAL CHARACTERISTICS at $V_S = \pm 15V$, $T_A = +25^\circ C$, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	OP-15NT	OP-15N	OP-15GT	OP-15G	OP-15GR	UNITS
			OP-16NT	OP-16N	OP-16GT	OP-16G	OP-16GR	
		OP-17NT TYPICAL	OP-17N TYPICAL	OP-17GT TYPICAL	OP-17G TYPICAL	OP-17GR TYPICAL		
Average Input Offset Drift Unnullled	TCV_{OS}		2	2	3	3	4	$\mu V^\circ C$
Average Input Offset Drift Nullled	TCV_{OSn}	$R_P = 100k\Omega$	2	2	3	3	4	$\mu V^\circ C$
Input Offset Current	I_{OS}		3	3	3	3	3	pA
Input Bias Current	I_B		± 15	± 15	± 15	± 15	± 15	pA
Slew Rate	SR	$AV_{CL} = +1$	OP-15	13	13	11	11	9
		OP-16	25	25	21	21	17	$V/\mu s$
		OP-17	60	60	50	50	40	
Settling Time (see settling time test circuits)	t_S	to 0.01%	4.5	4.5	4.5	4.5	4.7	
		to 0.05%	OP-15	1.5	1.5	1.5	1.5	1.6
		to 0.10%		1.2	1.2	1.2	1.2	1.3
		to 0.01%	3.8	3.8	3.8	3.8	4.0	
		to 0.05%	OP-16	1.2	1.2	1.2	1.2	1.3
		to 0.10%		0.9	0.9	0.9	0.9	1.0
		to 0.01%	1.5	1.5	1.5	1.5	1.6	
		to 0.05%	OP-17	0.7	0.7	0.7	0.7	0.8
		to 0.10%		0.6	0.6	0.6	0.6	0.7
		OP-15	6.0	6.0	5.7	5.7	5.4	
		OP-16	8.0	8.0	7.6	7.6	7.2	MHz
		OP-17	30	30	28	28	26	
Closed-Loop Bandwidth	CLBW	$AV_{CL} = +1$	OP-15	14	14	13	13	12
		OP-16	19	19	18	18	17	MHz
		OP-17	11	11	10	10	9	
Input Noise Voltage Density	e_n	f = 100Hz	20	20	20	20	20	
		f = 1000Hz	15	15	15	15	15	nV/ \sqrt{Hz}
Input Noise Current Density	i_n	f = 100Hz	0.01	0.01	0.01	0.01	0.01	
		f = 1000Hz	0.01	0.01	0.01	0.01	0.01	pA/ \sqrt{Hz}
Input Capacitance	C_{IN}		3	3	3	3	3	pF

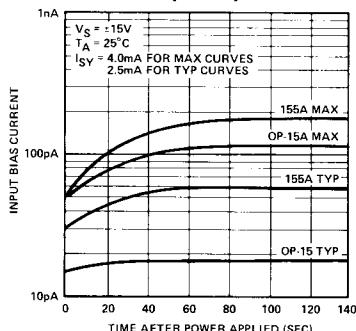
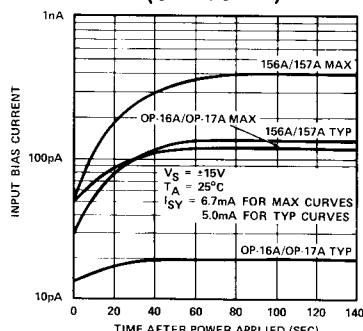
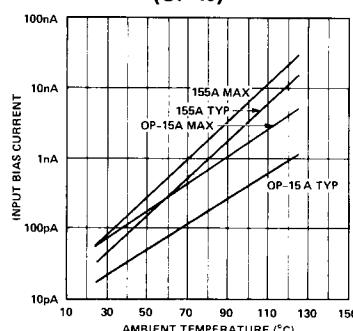
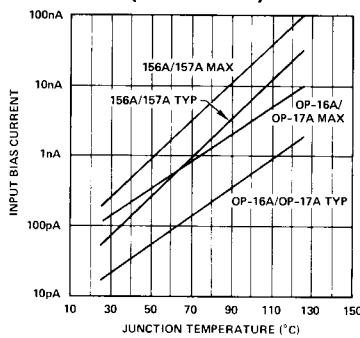
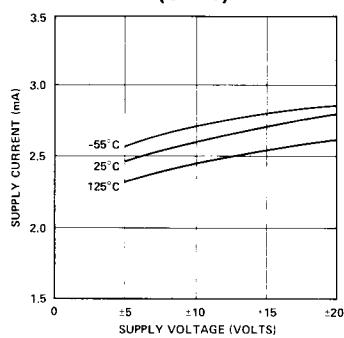
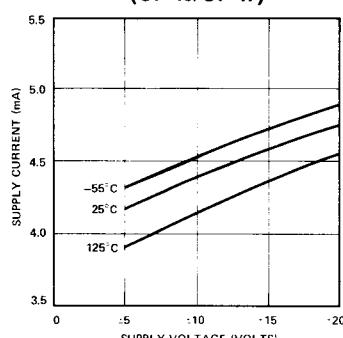
NOTES:

For $25^\circ C$ characteristics of OP-15/16/17NT and OP-15/16/17GT, see OP-15/16/17N and OP-15/16/17G characteristics, respectively.

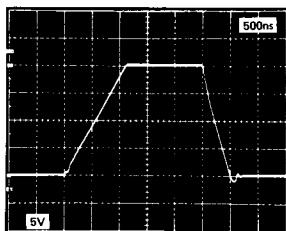
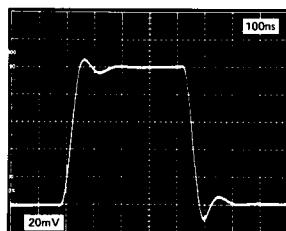
TYPICAL PERFORMANCE CHARACTERISTICS (OP-15/OP-16/OP-17)



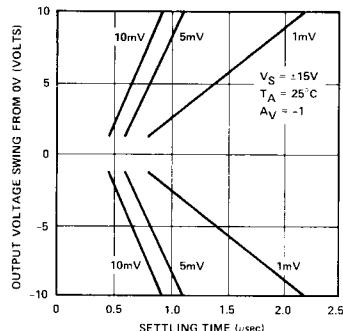
TYPICAL PERFORMANCE CHARACTERISTICS (OP-15/OP-16/OP-17)

BIAS CURRENT vs TIME
IN FREE AIR
(OP-15)BIAS CURRENT vs TIME
IN FREE AIR
(OP-16/OP-17)INPUT BIAS CURRENT vs
AMBIENT TEMPERATURE (UNITS
ARE WARMED-UP IN FREE AIR)
(OP-15)INPUT BIAS CURRENT vs
AMBIENT TEMPERATURE (UNITS
ARE WARMED-UP IN FREE AIR)
(OP-16/OP-17)SUPPLY CURRENT
vs SUPPLY VOLTAGE
(OP-15)SUPPLY CURRENT
vs SUPPLY VOLTAGE
(OP-16/OP-17)

TYPICAL PERFORMANCE CHARACTERISTICS (OP-15)

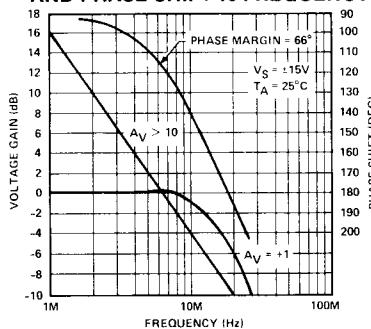
LARGE-SIGNAL
TRANSIENT RESPONSESMALL-SIGNAL
TRANSIENT RESPONSE

SETTLING TIME

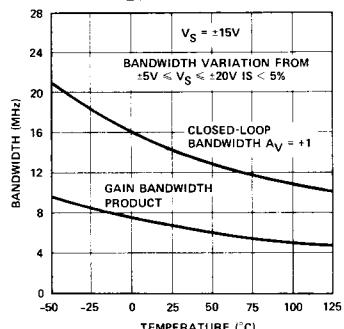


TYPICAL PERFORMANCE CHARACTERISTICS (OP-15)

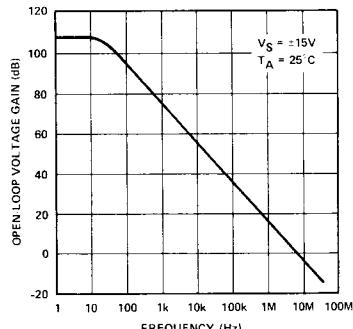
CLOSED-LOOP BANDWIDTH AND PHASE SHIFT vs FREQUENCY



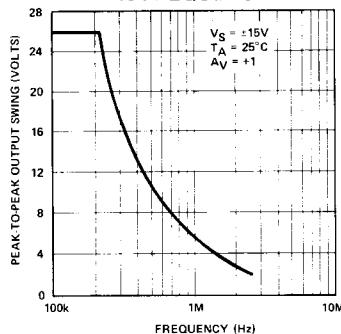
BANDWIDTH vs TEMPERATURE



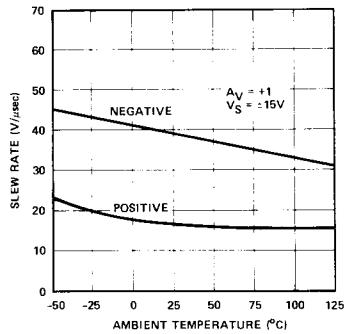
OPEN-LOOP GAIN vs FREQUENCY



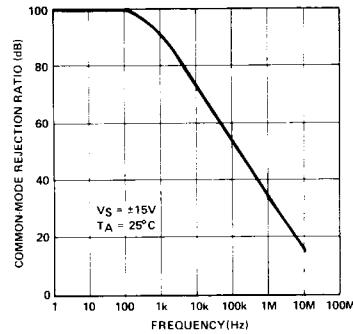
MAXIMUM OUTPUT SWING vs FREQUENCY



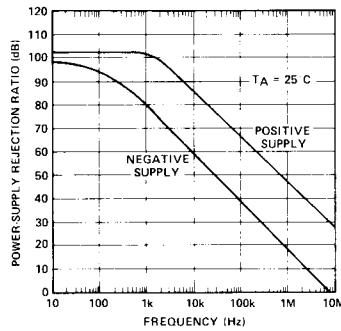
SLEW RATE vs TEMPERATURE



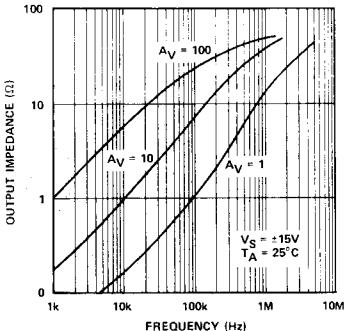
COMMON-MODE REJECTION RATIO vs FREQUENCY



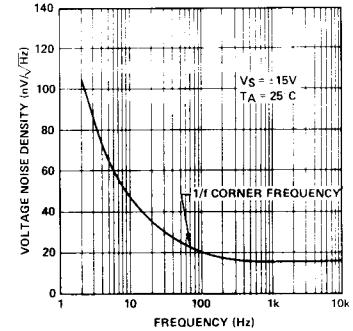
POWER-SUPPLY REJECTION RATIO vs FREQUENCY



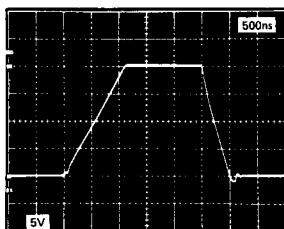
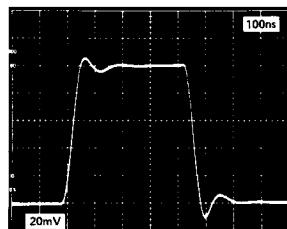
OUTPUT IMPEDANCE vs FREQUENCY



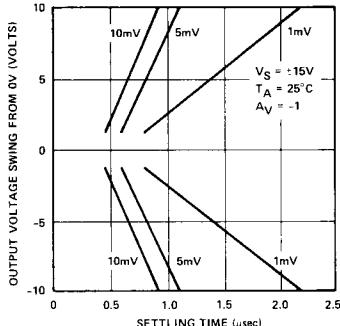
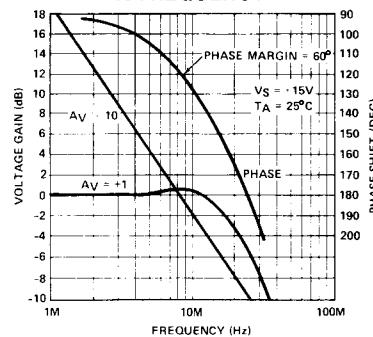
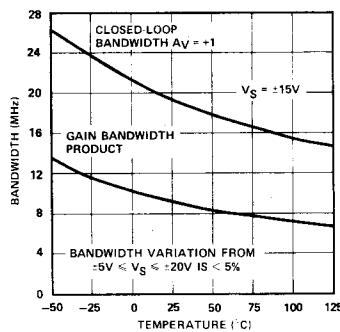
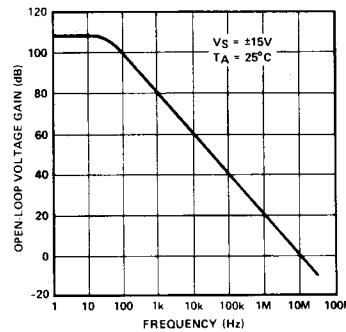
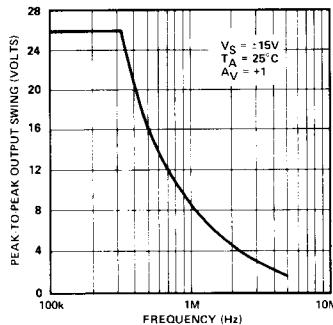
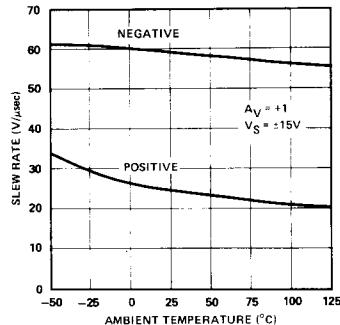
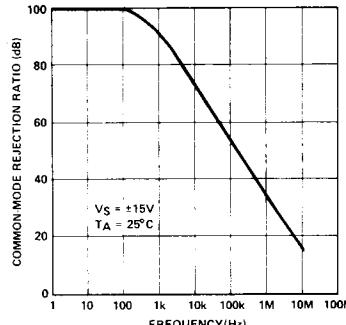
VOLTAGE NOISE DENSITY vs FREQUENCY



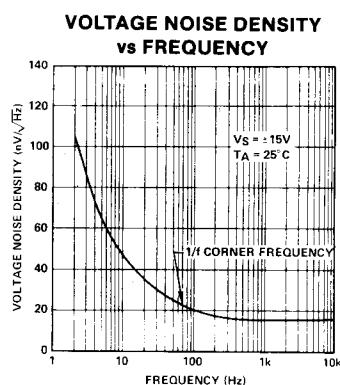
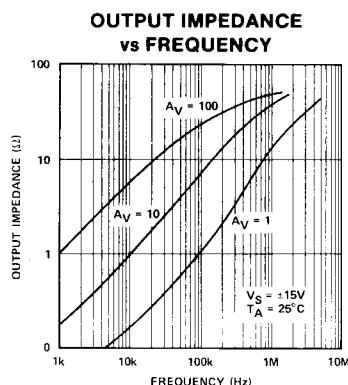
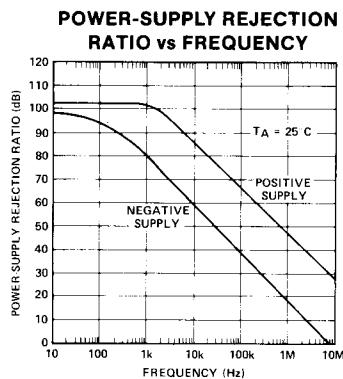
TYPICAL PERFORMANCE CHARACTERISTICS (OP-16)

LARGE-SIGNAL
TRANSIENT RESPONSESMALL-SIGNAL
TRANSIENT RESPONSE

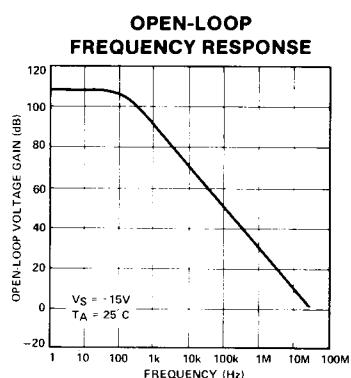
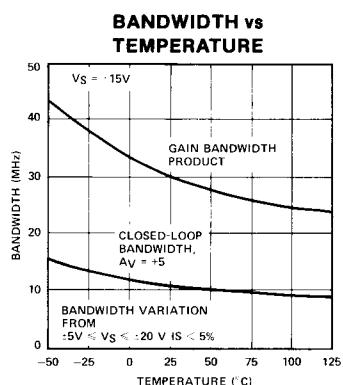
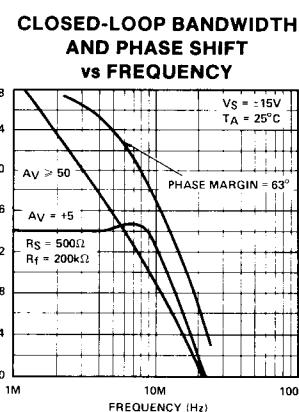
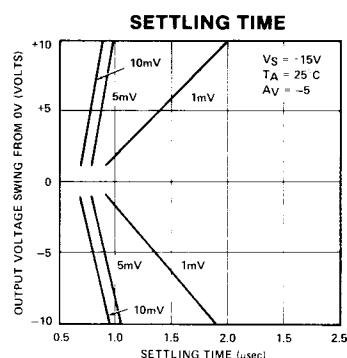
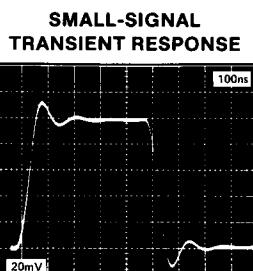
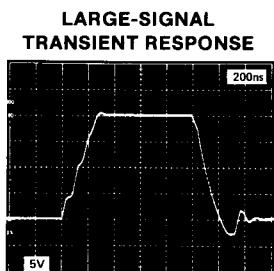
SETTLING TIME

CLOSED-LOOP BANDWIDTH
AND PHASE SHIFT
vs FREQUENCYBANDWIDTH vs
TEMPERATUREOPEN-LOOP GAIN
vs FREQUENCYMAXIMUM OUTPUT SWING
vs FREQUENCYSLEW RATE
vs TEMPERATURECOMMON-MODE REJECTION
RATIO vs FREQUENCY

TYPICAL PERFORMANCE CHARACTERISTICS (OP-16)

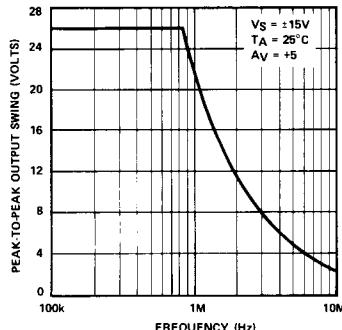


TYPICAL PERFORMANCE CHARACTERISTICS (OP-17)

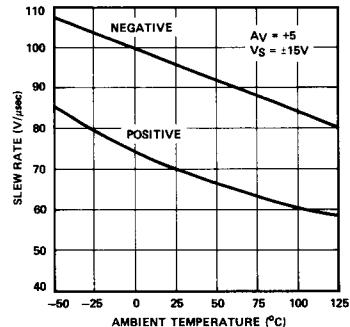


TYPICAL PERFORMANCE CHARACTERISTICS (OP-17)

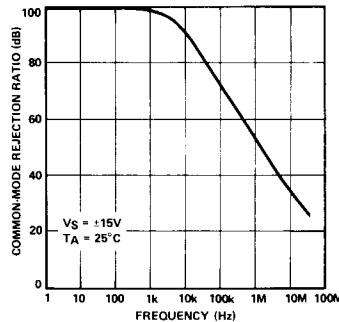
MAXIMUM OUTPUT SWING vs FREQUENCY



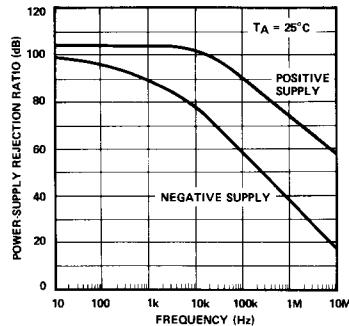
SLEW RATE vs TEMPERATURE



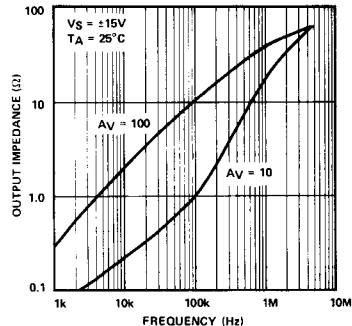
COMMON-MODE REJECTION RATIO vs FREQUENCY



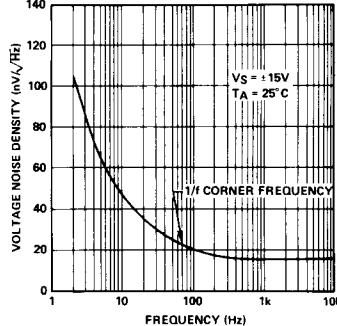
POWER-SUPPLY REJECTION RATIO vs FREQUENCY



OUTPUT IMPEDANCE vs FREQUENCY

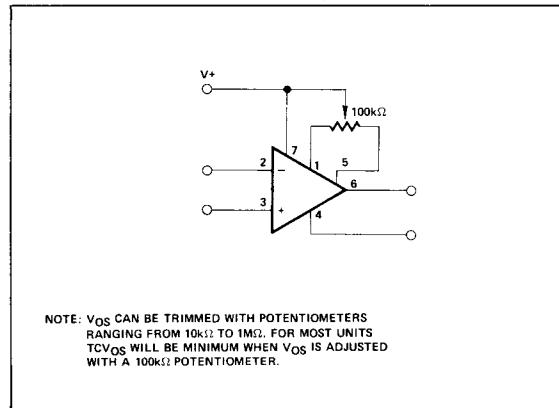


VOLTAGE NOISE vs FREQUENCY

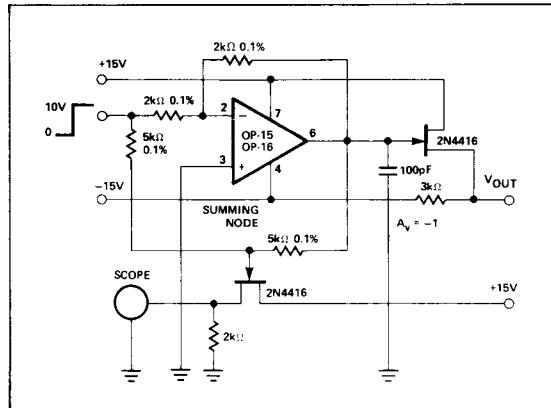


BASIC CONNECTIONS

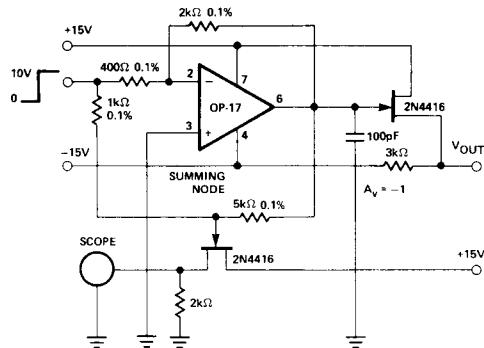
INPUT OFFSET VOLTAGE NULLING



SETTLING-TIME TEST CIRCUIT — OP-15/OP-16

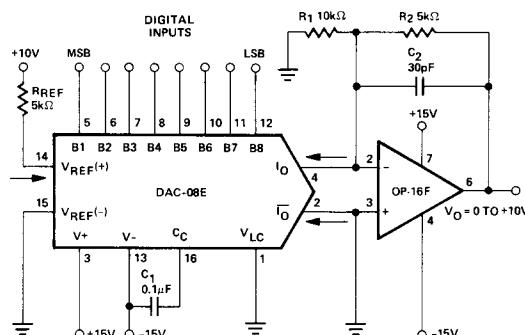


SETTLING-TIME TEST CIRCUIT — OP-17



TYPICAL APPLICATIONS

CURRENT-TO-VOLTAGE AMPLIFIER OUTPUT



APPLICATIONS INFORMATION

DYNAMIC OPERATING CONSIDERATIONS

As with most amplifiers, care should be taken with lead dress, component placement, and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pick-up" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance

from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3dB frequency of the closed-loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately six times the expected 3dB frequency, a lead capacitor should be placed from the output to the negative input of the op amp. The value of the added capacitor should be such that the RC time-constant of this capacitor and the resistance it parallels is greater than, or equal to, the original feedback pole time constant.